

UNITED STATES PATENT AND TRADEMARK OFFICE
CERTIFICATE OF CORRECTION

PATENT NO. : 7,019,342 B2
APPLICATION NO. : 10/719119
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INVENTOR(S) : Douglas R. Hackler, Sr. et al.

Page 1 of 1

It is certified that error appears in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

Column 1, line 38, "... inputs values ..." change to --input values--

Column 1, line 39, "... output value of 0 ..." change to
--outputs a value of 0--

Column 1, line 49, "... overall architecture" change to --overall architecture.--

Column 2, line 18, "... gates result ..." change to --gate result--

Column 2, line 21, "... bottom gates ..." change to --bottom gate--

Column 3, line 1-2, "... device of FIG. 13 device after ..." change to --device
of FIG. 13 after--

Column 7, line 46, "... to FIG. 12 to, a method ..." change to --to FIG. 12, a
method--

Column 7, line 60, "... the substrate layer 12 ..." change to --the SOI layer
16--

Column 10, line 21, "... numerous complex circuit ..." change to --numerous
complex circuits--

Signed and Sealed this

Sixteenth Day of January, 2007



JON W. DUDAS
Director of the United States Patent and Trademark Office